TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2$ - $\pi$ -MOSVI)

# **2SJ537**

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : RDS (ON) = 0.16  $\Omega$  (typ.)

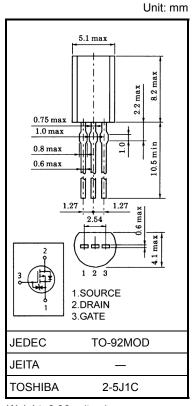
 $\bullet~$  High forward transfer admittance ~ :  $|\,Y_{fs}\,|\,$  = 3.5 S (typ.)

• Low leakage current :  $I_{DSS} = -100 \,\mu\text{A} \,(V_{DS} = -50 \,\text{V})$ 

• Enhancement-mode :  $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA)}$ 

#### Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-50	٧	
Drain-gate voltage (Ro	<sub>GS</sub> = 20 kΩ)	$V_{DGR}$	-50	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	-5	Α	
	Pulse (Note 1)	$I_{DP}$	-15	Α	
Drain power dissipation	า	P <sub>D</sub>	0.9	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.

Please handle with caution.

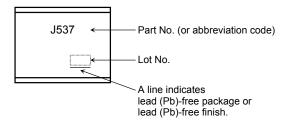
### **Electrical Characteristics (Ta = 25°C)**

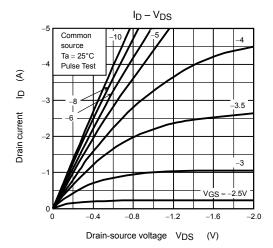
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = 0 V	_	_	-100	μΑ
Drain-source br voltage	reakdown	V (BR) DSS	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-50	_	_	V
Gate threshold v	/oltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	_	-2.0	V
Drain-source O	N registance	Pro (ON)	$V_{GS} = -4 \text{ V}, I_D = -1.3 \text{ A}$	_	0.27	0.34	
Drain-source ON resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.5 A	_	0.16	0.19	Ω	
Forward transfe	r admittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	1.5	3.5	-	S
Input capacitano	ce	C <sub>iss</sub>		_	470	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	60	_	pF
Output capacitance		C <sub>oss</sub>			210	_	
Switching time	Rise time	t <sub>r</sub>	$V_{GS}_{-10V}$ $I_{D}=-2.5A$ $R_{L}=10\Omega$	_	25	_	ns
	Turn-on time	t <sub>on</sub>		_	35	_	
	Fall time	t <sub>f</sub>		_	20	_	
	Turn-off time	toff	$V_{DD} = -25V$ Duty $\leq 1\%$ , $t_W = 10 \mu s$	_	120	-	
Total gate charge (Gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -40 V, V <sub>GS</sub> = -10 V,	_	18	_	
Gate-source charge		Q <sub>gs</sub>	I <sub>D</sub> = -5 A	_	13	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	5	_	

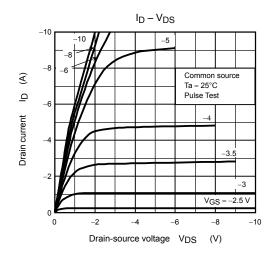
## Source-Drain Ratings and Characteristics (Ta = 25°C)

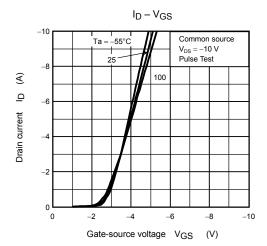
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	-5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	-15	Α
Forward voltage (diode)	$V_{DSF}$	$I_{DR}$ = -5 A, $V_{GS}$ = 0 V	1	_	1.5	V

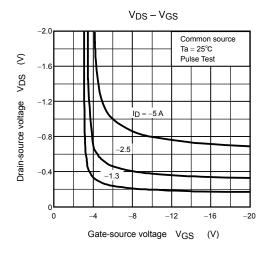
### Marking

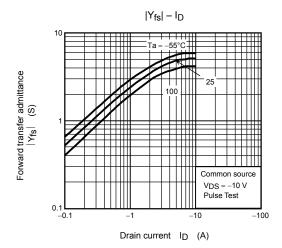


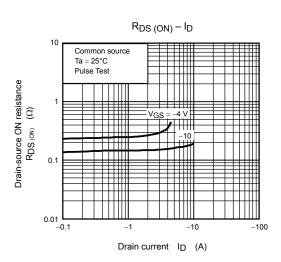




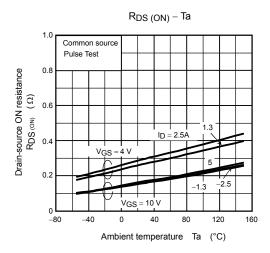


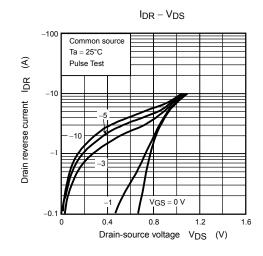


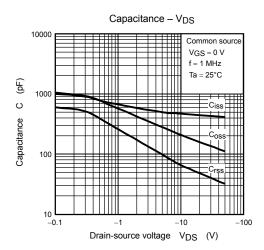


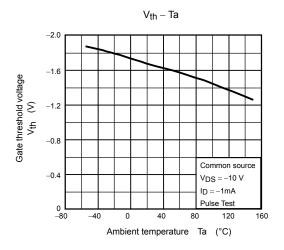


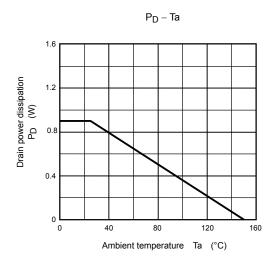
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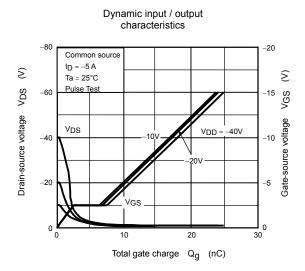


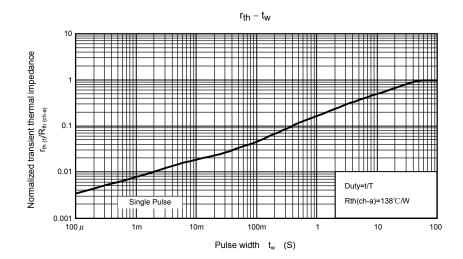


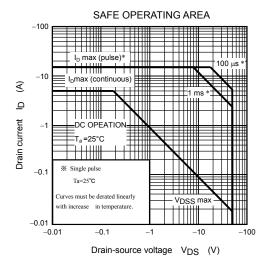












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